NSN 5961-01-106-7627

Thyristor Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-106-7627	
Inclosure Material:	
Metal	
Overall Length:	
Between 0.170 inches and 0.210 inches	
Terminal Length:	
Between 0.500 inches and 0.750 inches	
Overall Diameter:	
Between 0.209 inches and 0.230 inches	
Internal Configuration:	
Junction contact	
Joint Electronic Device Engineering Council/jedec/case Outline Designation:	
To-18	
Electrode Internally-electrically Connected To Case:	
Gate	
Mounting Method:	
Terminal	
Terminal Circle Diameter:	
0.100 inches	
Features Provided:	
Hermetically sealed case	
Semiconductor Material:	
Silicon	
Voltage Rating In Volts Per Characteristic:	
40.0 gate voltage, dc	
Current Rating Per Characteristic:	
5.00 amperes forward current, average preset	
Power Rating Per Characteristic:	
0.3 watts small-signal input power, common-collector preset	
Maximum Operating Tempurature Per Measurement Point:	
150.0 degrees celsius ambient air	
Special Features:	
Internal junction configuration arrangement pnpn	
Test Data Document:	
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specific	ation
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain	
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).	
Terminal Type And Quantity:	
3 uninsulated wire lead	
Specification Data:	
81349-mil-s-19500/493 government specification	
Shelf Life:	
N/a	

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Unit Of Measure:

NSN 5961-01-106-7627

Thyristor Semiconductor Device - Page 2 of 2



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No

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